

ABSTRACT OF THE DISCLOSURE

Disclosed is a semiconductor device comprising
a semiconductor substrate, a porous insulating film
formed above the semiconductor substrate, the porous
insulating film having a relative dielectric constant
of 2.5 or less and including a first insulating
material, at least a portion of pores in the porous
insulating film having on the inner wall thereof
a layer of a second insulating material which differs
in nature from the first insulating material, and
a plug and/or a wiring layer buried in the porous
insulating film.